

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS154

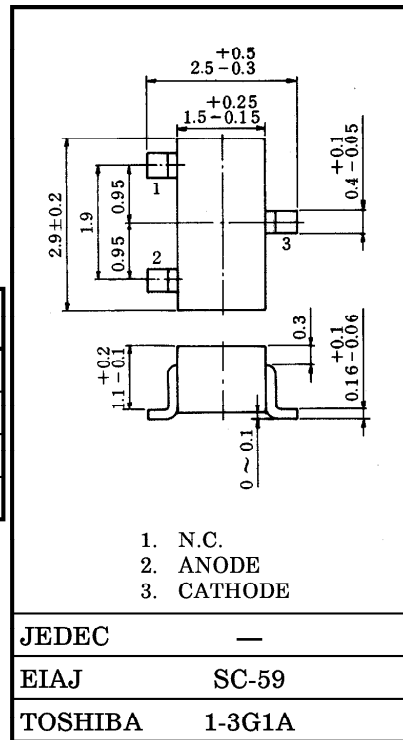
UHF~S BAND MIXER / DETECTOR APPLICATIONS

Unit in mm

- Small Package.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	6	V
Forward Current	I_F	30	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-30~125	°C

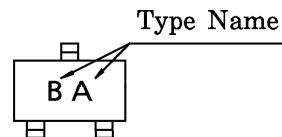


Weight : 0.012g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	$I_R = 10\mu A$	6	—	—	V
Reverse Current	I_R	$V_R = 5V$	—	—	0.5	μA
Forward Voltage	$V_{F(1)}$	$I_F = 0.1mA$	—	—	0.35	V
Forward Voltage	$V_{F(2)}$	$I_F = 10mA$	—	0.5	—	V
Total Capacitance	C_T	$V_R = 0, f = 1MHz$	—	0.8	—	pF

Marking



961001EAA2

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